

APT1001RBNR 1000V 11.0A 1.00Ω
 APT1001R1BNR 1000V 10.5A 1.10Ω

POWER MOS IV®

UIS RATED

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT1001RBNR	APT1001R1BNR	UNIT
V _{DSS}	Drain-Source Voltage	1000	1000	Volts
I _D	Continuous Drain Current @ T _C = 25°C	11	10.5	Amps
I _{DM}	Pulsed Drain Current ^①	44	42	
V _{GS}	Gate-Source Voltage Continuous	±20		Volts
V _{GSM}	Gate-Source Voltage Transient	±30		
P _D	Total Power Dissipation @ T _C = 25°C	310		Watts
	Linear Derating Factor	2.5		W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150		°C
T _L	Lead Temperature: 0.063" from Case for 10 Sec.	300		
I _{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	11		Amps
E _{AR}	Repetitive Avalanche Energy ^①	25		mJ
E _{AS}	Single Pulse Avalanche Energy ^④	1210		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	1000			Volts
$I_{D(ON)}$	On State Drain Current ⁽²⁾ ($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT1001RBNR	11		Amps
		APT1001R1BNR	10.5		
$R_{DS(ON)}$	Drain-Source On-State Resistance ⁽²⁾ ($V_{GS} = 10V, 0.5 I_{D(ON)}$)	APT1001RBNR		1.00	Ohms
		APT1001R1BNR		1.10	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 20V, V_{DS} = 0V$)			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1.0mA$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.40	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient			40	

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

APT1001R/1001R1BNR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		3400	4000	pF
C_{oss}	Output Capacitance			330	500	
C_{rss}	Reverse Transfer Capacitance			126	190	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		150	210	nC
Q_{gs}	Gate-Source Charge			16	25	
Q_{gd}	Gate-Drain ("Miller") Charge			75	110	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		18	36	ns
t_r	Rise Time			22	45	
$t_d(\text{off})$	Turn-off Delay Time			110	160	
t_f	Fall Time			42	85	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT1001RBNR		11	Amps
		APT1001R1BNR		10.5	
I_{SM}	Pulsed Source Current ① (Body Diode)	APT1001RBNR		44	
		APT1001R1BNR		42	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}], dI_S/dt = 100A/\mu s$)	250	500	1000	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}], dI_S/dt = 100A/\mu s$)	2.5	5	10	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1 \text{ Sec.}$	310			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}], V_{DS} = P_D / I_D [\text{Cont.}], t = 1 \text{ Sec.}$	310			
I_{LM}	Inductive Current Clamped	APT1001RBNR	44			Amps
		APT1001R1BNR	42			

① Repetitive Rating: Pulse width limited by maximum junction temperature.

③ See MIL-STD-750 Method 3471

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%④ Starting $T_J = +25^\circ\text{C}$, $L = 20\text{mH}$, $R_G = 25\Omega$, Peak $I_L = 11A$

APT Reserves the right to change, without notice, the specifications and information contained herein.

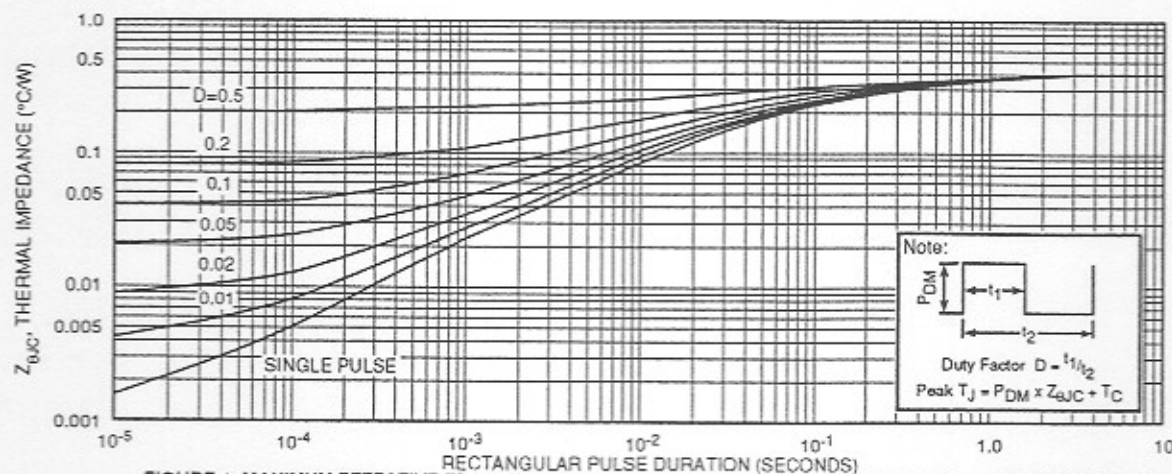


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

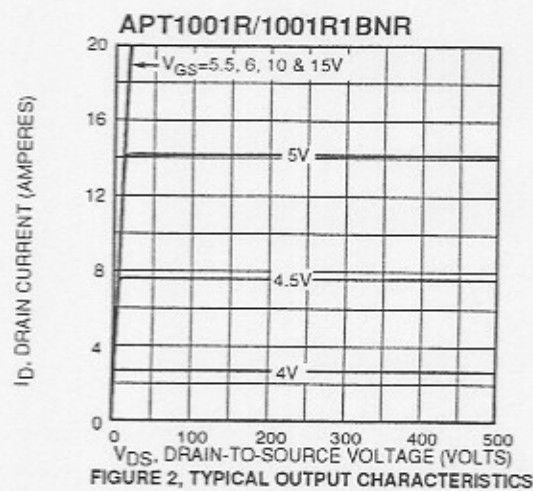


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

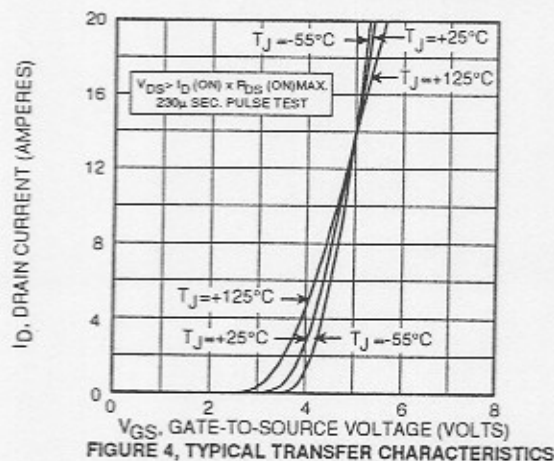


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

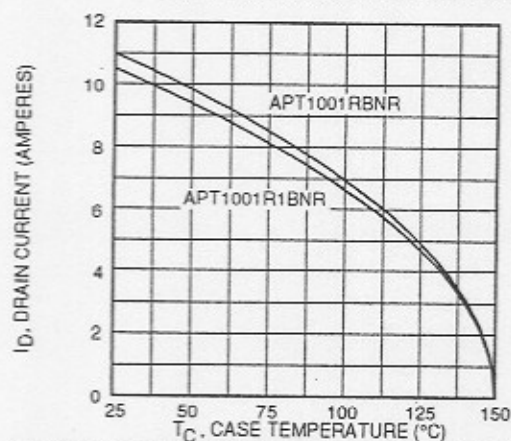


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

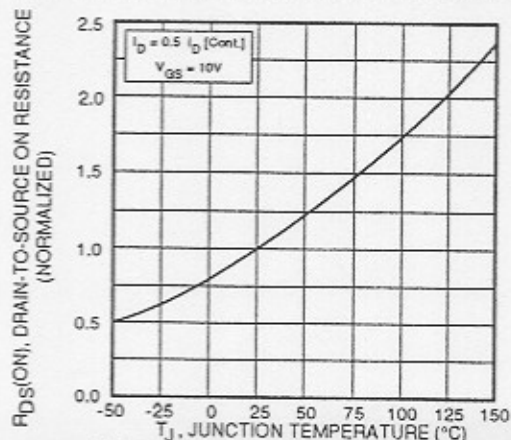


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

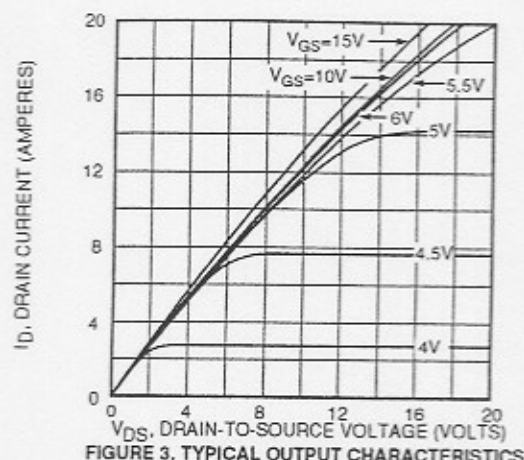


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

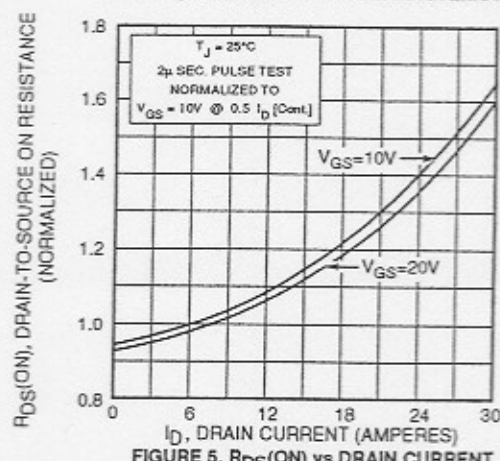


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

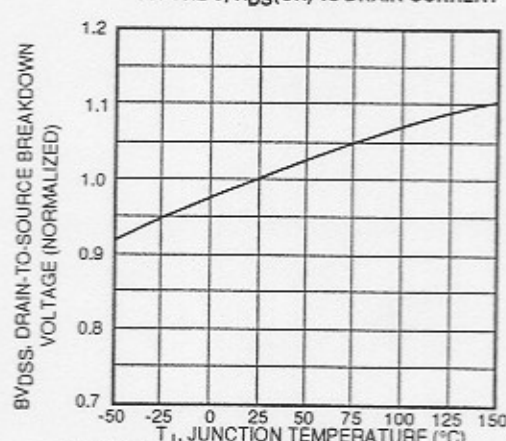


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

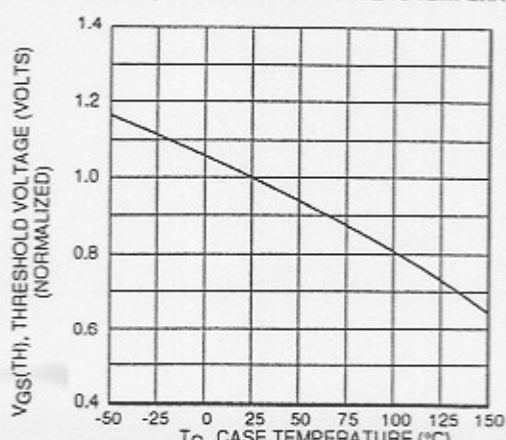


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

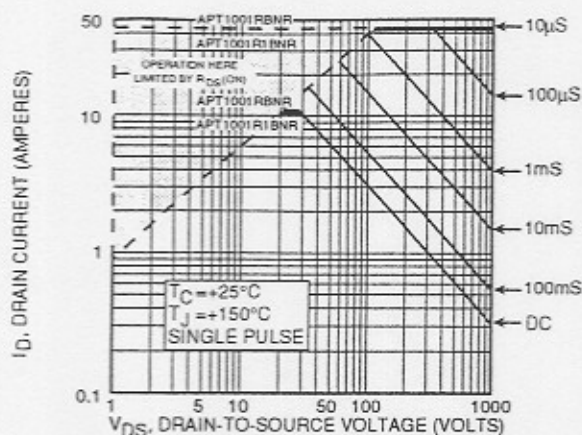


FIGURE 10, MAXIMUM SAFE OPERATING AREA

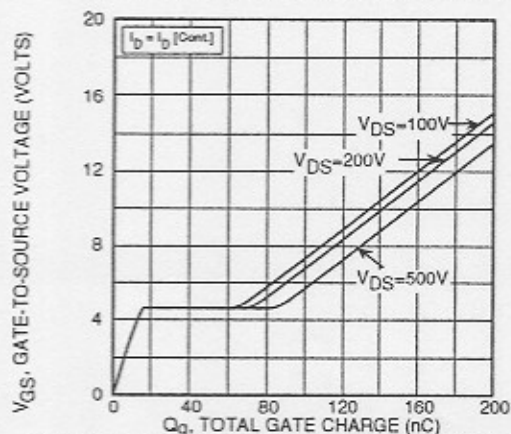


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

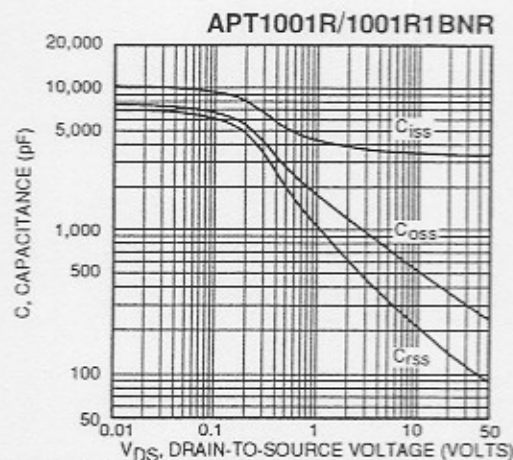


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

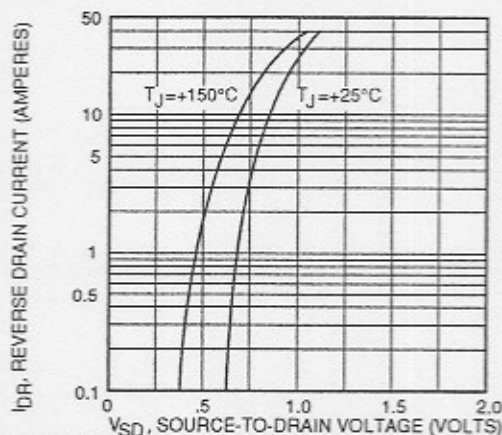


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247AD Package Outline

